

**AMENDMENTS TO THE CLAIMS**

Please amend the claims as follows:

1. (Currently Amended) A nitride semiconductor comprising:

a substrate;

a GaN-based buffer layer formed on the substrate in any one selected from a group consisting of a three-layered structure  $\text{Al}_y\text{In}_x\text{Ga}_{1-(x+y)}\text{N}/\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$  and  $0 \leq y \leq 1$ , a two-layered structure  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$ , and a superlattice structure of  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$ ; and

a GaN-based single crystalline layer formed on the GaN-based buffer layer.

2. (Original) The nitride semiconductor of claim 1, wherein the GaN-based single crystalline layer comprises:

an indium-doped GaN layer;

an undoped GaN layer formed on the Indium-doped GaN layer; and

a silicon-doped n-GaN layer formed on the undoped GaN layer.

3. (Original) The nitride semiconductor of claim 1, wherein the GaN-based single crystalline layer comprises:

an undoped GaN layer;

an indium-doped GaN layer formed on the undoped GaN layer; and

a silicon-doped n-GaN layer formed on the indium-doped GaN layer.

4. (Currently Amended) A nitride semiconductor light emitting device comprising:

- a substrate;
- a GaN-based buffer layer formed on the substrate in any one selected from a group consisting of a three-layered structure  $\text{Al}_y\text{In}_x\text{Ga}_{1-(x+y)}\text{N}/\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$  and  $0 \leq y \leq 1$ , a two-layered structure  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$ , and a superlattice structure of  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$ ;
- a first electrode layer of an n-GaN layer formed on the GaN-based buffer layer;
- an activation layer formed on the first electrode layer; and
- a second electrode layer of a p-GaN layer formed on the activation layer.

5. (Original) The nitride semiconductor light emitting device of claim 4, further comprising:

- an Indium-doped GaN layer formed on the GaN-based buffer layer; and
- an undoped GaN layer formed on the Indium-doped GaN layer.

6. (Original) The nitride semiconductor light emitting device of claim 4, further comprising:

- an undoped GaN layer formed on the GaN-based buffer layer; and
- an Indium-doped GaN layer formed on the undoped GaN layer.

7. (Currently Amended) A method for fabricating a nitride semiconductor, the method comprising the steps of:

(a) growing a GaN-based buffer layer on a substrate in any one selected from a group consisting of a three-layered structure  $\text{Al}_y\text{In}_x\text{Ga}_{1-(x+y)}\text{N}/\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$  and  $0 \leq y \leq 1$ , a two-layered structure  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$ , and a superlattice structure of  $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$  where  $0 < x \leq 1$ ; and

(b) growing a GaN-based single crystalline layer on the grown GaN-based buffer layer.

8. (Original) The method of claim 7, wherein the GaN-based buffer layer is grown in an MOCVD equipment at a temperature of 500 – 800 °C and in a thickness of 50 – 800 Å by introducing sources of TMGa, TMIIn and TMAI and a gas of  $\text{NH}_3$  at the same time while supplying carrier gases of  $\text{H}_2$  and  $\text{N}_2$ .

9. (Previously Presented) The method of claim 8, wherein the GaN-based buffer layer is grown under a condition that flow of the sources of TMGa, TMIIn and TMAI is 5 – 300  $\mu\text{mol}/\text{min}$  and growing pressure is 100 – 700 torr.

10. (Original) The method of claim 7, wherein the step (b) comprises the steps of:  
growing an Indium-doped GaN layer;  
growing an undoped GaN layer on the Indium-doped GaN layer; and  
growing a silicon-doped n-GaN layer on the undoped GaN layer.

11. (Original) The method of claim 7, wherein the step (b) comprises the steps of:  
growing an undoped GaN layer;  
growing an Indium-doped GaN layer on the undoped GaN layer; and  
growing a silicon-doped n-GaN layer on the Indium-doped GaN layer.

12. (Previously Presented) The nitride semiconductor of claim 1, wherein the GaN-based buffer layer is grown in an MOCVD equipment at a temperature of 500 – 800 °C and in a thickness of 50 – 800 Å by introducing sources of TMGa, TMIIn and TMAI and a gas of NH<sub>3</sub> at the same time while supplying carrier gases of H<sub>2</sub> and N<sub>2</sub>.

13. (Previously Presented) The nitride semiconductor of claim 12, wherein the GaN-based buffer layer is grown under a condition that flow of the sources of TMGa, TMIIn and TMAI is 5 – 300 μmol/min and growing pressure is 100 – 700 torr.

14. (Previously Presented) The nitride semiconductor light emitting device of claim 4, wherein the GaN-based buffer layer is grown in an MOCVD equipment at a temperature of 500 – 800 °C and in a thickness of 50 – 800 Å by introducing sources of TMGa, TMIIn and TMAI and a gas of NH<sub>3</sub> at the same time while supplying carrier gases of H<sub>2</sub> and N<sub>2</sub>.

15. (Previously Presented) The nitride semiconductor light emitting device of claim 14, wherein the GaN-based buffer layer is grown under a condition that flow of the sources of TMGa, TMIIn and TMAI is 5 – 300 μmol/min and growing pressure is 100 – 700 torr.